



37 CFR 1.501 INFORMATION DISCLOSURE STATEMENT IN A PATENT (use several sheets if necessary)					Docket No. P97.0322		Serial No. 08/809,463	
					Applicants Nakamura et al.			
					Filing Date April 21, 1997		Group Art Unit	
U.S. PATENT DOCUMENTS								
Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date If appropriate	
MC	AA	4,833,042	5/23/89	Waldrop et al.				
MC	AB	5,089,738	2/18/92	Katz				
MC	AC	5,027,187	6/25/91	O'Mara, Jr. et al.				
	AD						RECEIVED DEC 16 1997 GROUP 2500	
	AE							
	AF							
	AG							
	AH							
	AI							
	AJ							
	AK							
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							
	AQ							
	AR							
	AS							
OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
MC	AT	IEEE ELECTRON DEVICE LETTERS, vol. EDL6, no. 8, August 1985, pp. 437-438, XP002033693, R.D. Remba et al., "Use of TiN barrier to improve GaAs FET ohmic contact reliability".						
MC	AU	JOURNAL OF APPLIED PHYSICS, vol. 68, no. 5, September 1, 1990, pp. 2475-2481, XP000108786, Kim H.-J et al. "Thermally Stable Ohmic Contacts To N-Type GAAS. VIII Sputter-Deposited INAS Cotnacts."						
	AV							
	AW							
Examiner <i>M. Kelley</i>				Date Considered <i>2/98</i>				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								